

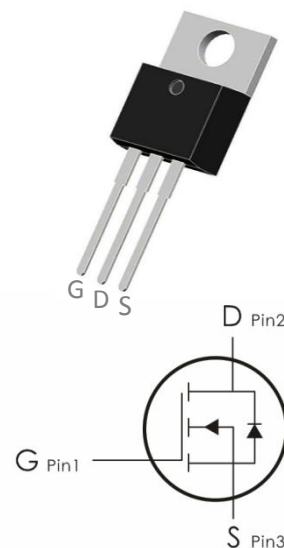
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=80V, I_D=96A, R_{DS(ON)} < 7.2m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOP95N08	95N08	TO- 220	50 pcs/Tube

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ\text{C}$	96	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	67	
I_{DM}	Pulsed Drain Current ¹	368	
P_D	Power Dissipation	146	W
E_{AS}	Single pulse avalanche energy ²	625	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+175	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.02	$^\circ\text{C}/\text{W}$

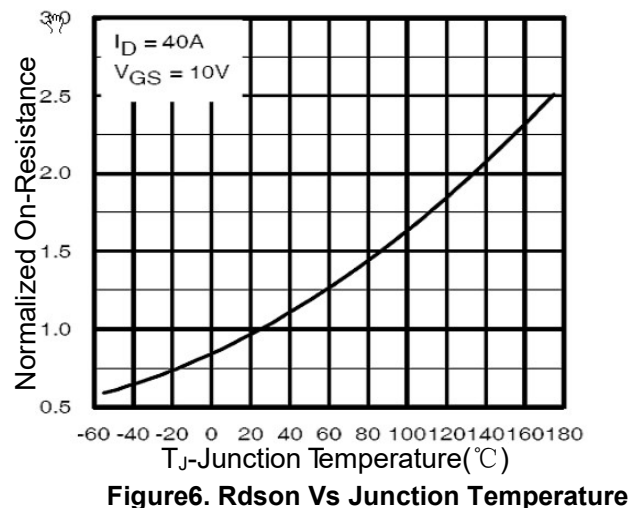
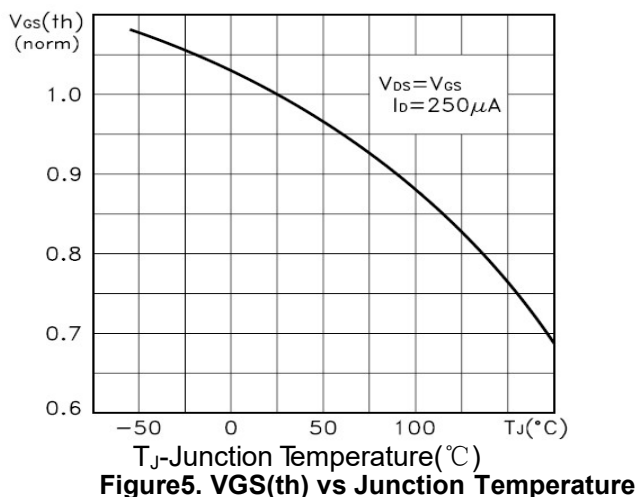
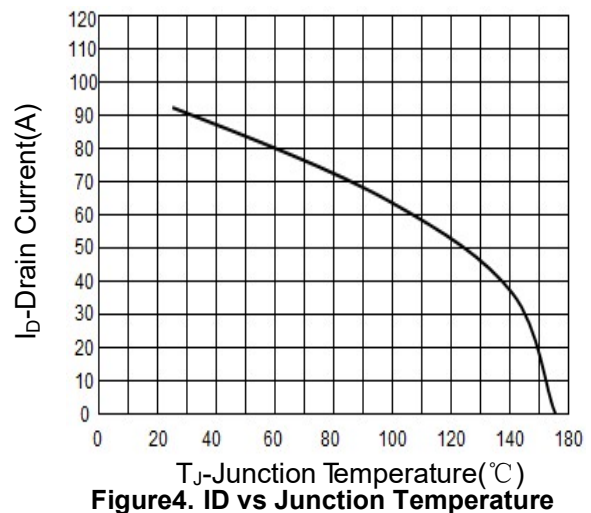
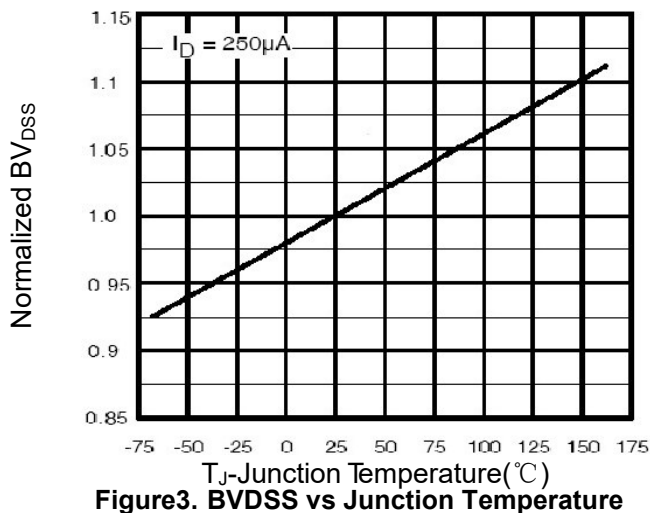
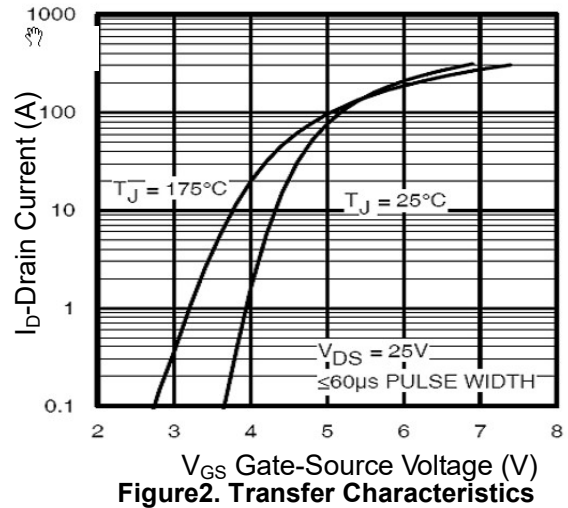
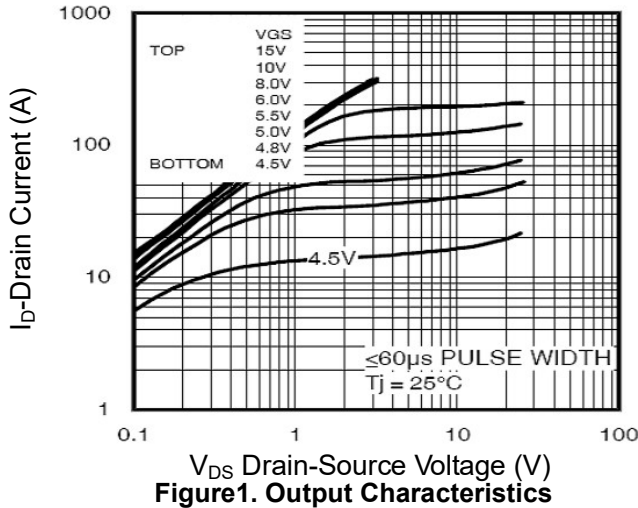
Electrical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

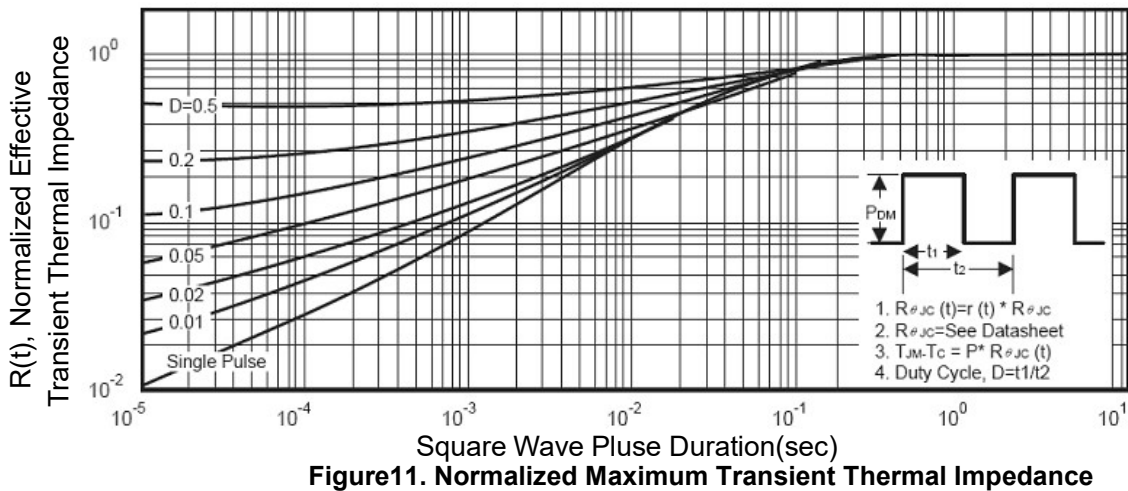
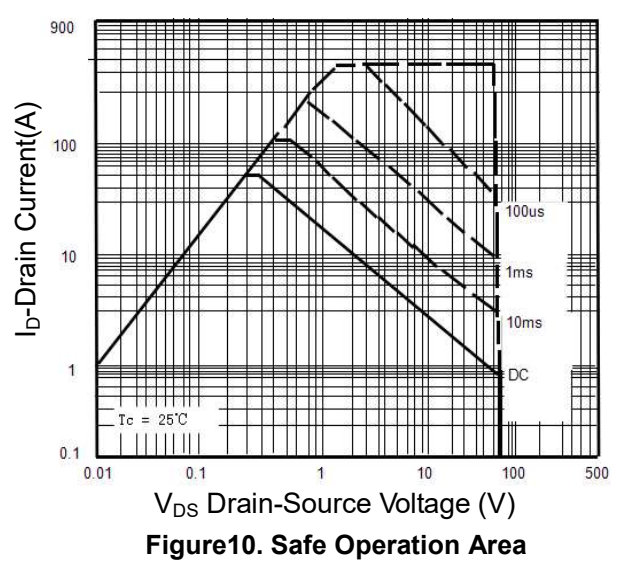
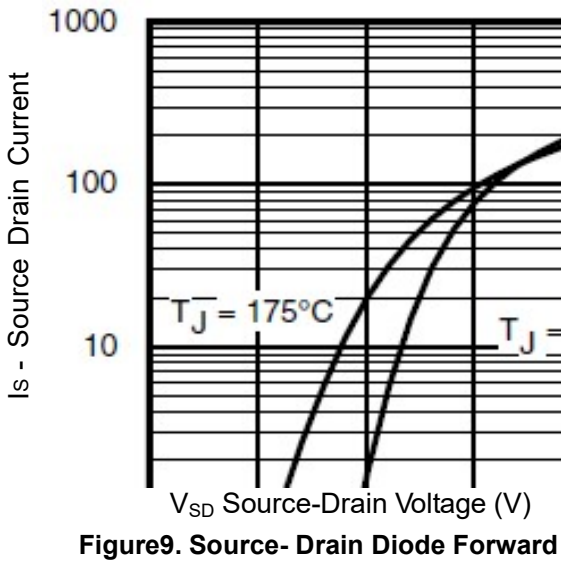
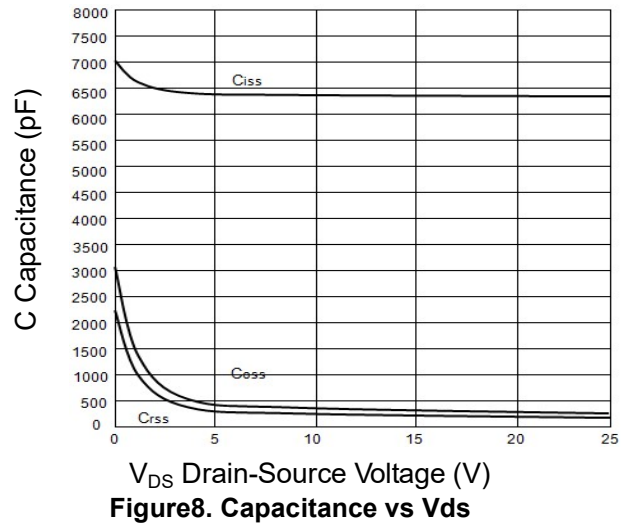
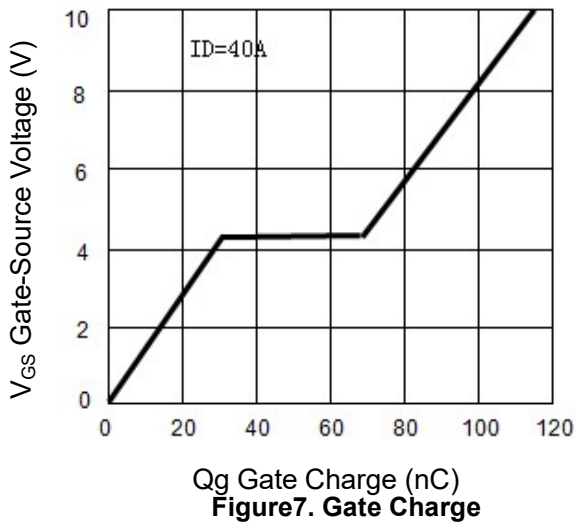
Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	80	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =80V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	2	---	4	V
R _{DS(ON)}	Drain-Source On Resistance ¹	V _{GS} =10V, I _D =40A	---	6.2	7.2	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	6395	---	pF
C _{oss}	Output Capacitance		---	386	--	
C _{rss}	Reverse Transfer Capacitance		---	255	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =30V, I _D =40A, R _{ENG} =2.5 Ω ,V _{GS} =10V	---	22	---	ns
t _r	Rise Time		---	50	---	ns
t _{d(off)}	Turn-Off Delay Time		---	65	---	ns
t _f	Fall Time		---	22	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =40A	---	116	---	nc
Q _{gs}	Gate-Source Charge		---	27	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	39	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _{SD} =40A	---	0.89	0.99	V
I _S	Continuous Drain Curren	VD=VG=0V	---	---	96	A
I _{SM}	Pulsed Drain Current		---	---	368	A
Trr	Reverse Recovery Time ³	I _F =75A, T _J =25 °C	---	41	---	ns
Qrr	Reverse Recovery Charge ³	dI/dt=100A/us	---	86	---	nc

Notes:

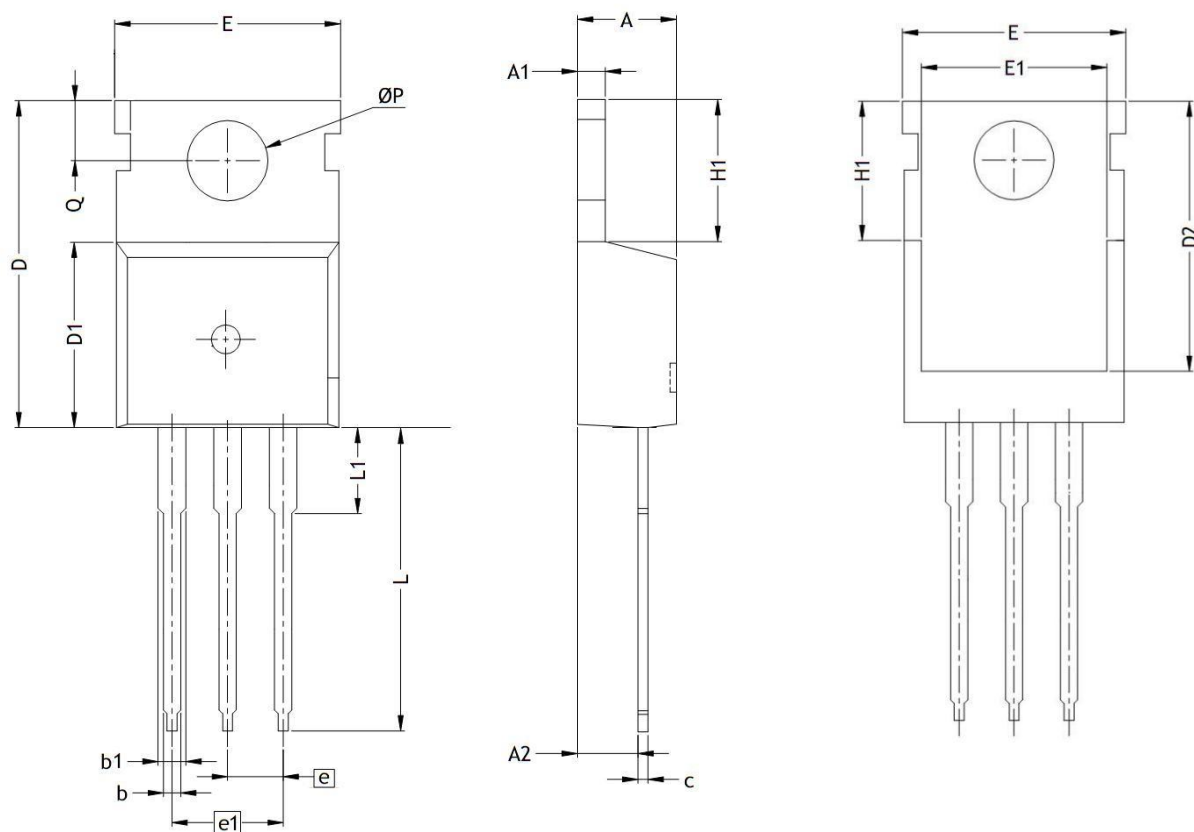
- 1.Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=40\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$
- 3.Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$

Typical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)





TO-220 Package Information:



UNIT: mm

SYMBOLS	A	A1	A2	b	b1	c	D	D1	D2	E	E1	e
MIN	4.25	1.25	2.35	0.7	1.15	0.45	14.35	8.80	13.05	9.90	7.85	2.540
MAX	4.65	1.35	2.55	0.9	1.75	0.60	15.95	9.50	13.65	10.35	8.85	BSC
SYMBOLS	e1	H1	L	L1	Q	φP						
MIN	5.080	6.30	12.85	2.85	2.70	3.50						
MAX	BSC	6.65	13.50	3.25	2.90	3.70						

Marking Information:

①. Doingter LOGO

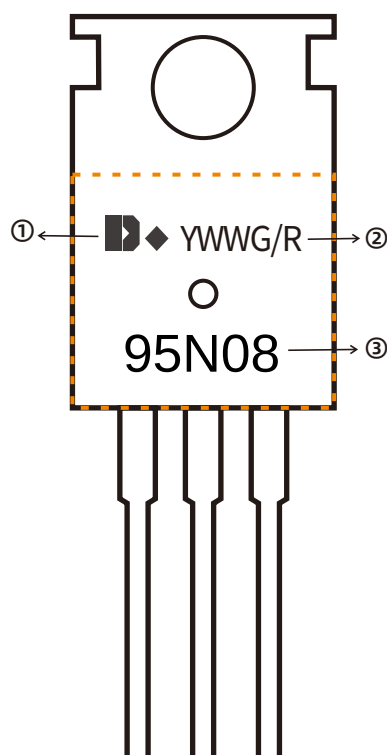
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



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